

Substitute for form 1449A/PTO			Complete (if Known)	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	10/642,305
			Filing Date	August 18, 2003
			First Named Inventor	Hongyong ZHANG et al.
			Art Unit	2811
			Examiner Name	D. Owens
			Attorney Docket Number	740756-2646

U.S. PATENT DOCUMENTS						
Examiner Initials	Chg No.	U.S. Patent Document Number - Kind Code ¹ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Chgd Document	Pages, Col Relevant to Fig.	See Notes, Where pages or Relevant to Appear
DWO		US-4,680,609	07/14/1987	Calder et al.		
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		US-4,882,295	11/21/1989	Czubatyj et al.		
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	US-4,693,759	09/15/1987	Noguchi et al.			
	US-4,459,739	07/17/1984	Shepherd et al.			

Examiner Signature	Douglas W. Owens	Date Considered	11/16/04
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Chp No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patent or Application of Claim Document	Page, Column, Line, Where Relevant Passages or Relevant Figures Appear	Type
		Country Code ²	Number ³ (if known)				
DAZ		JP	62-211165	09/1987			Abstract
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		GB	2169442 A	07/09/1986			Full
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		JP	61-183970	08/16/1986			Abstract
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		JP	01-283873	11/15/1989			Abstract
		JP	02-303030	12/17/1990			Abstract
		JP	60-043869	01/08/1985			Abstract
		JP	02-159069	06/19/1990			Abstract
		JP	02-148831	06/07/1990			Abstract
		JP	01-187814	07/27/1989			Abstract
		JP	60-245174	12/04/1985			Abstract
		JP	60-018913	01/31/1985			Abstract
		JP	62-285469	12/11/1987			Abstract
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		JP	01-209764	08/23/1989	Kato		Ex. Cited
		JP	02-090568	03/30/1990	Suyama		Ex. Cited
		EP	436 741	07/17/1991	Ando et al.		Ex. Cited
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		JP	62-285469	03/25/1988	Abe		Ex. Cited
		JP	62-244165	10/24/1987			Abstract
		JP	01-187873	07/27/1989			Abstract
		JP	01-287964	11/20/1989			Abstract & Full
		JP	01-042864	02/15/1989			Abstract
		JP	01-268064	10/25/1989			Full
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		JP	61-198678	09/03/1986	Yanagisawa		Abstract
		JP	63-036574	02/17/1988	Konishi et al.		Abstract
DAZ		JP	55-163848	12/20/1980			Full

Examiner Signature	<i>Douglas K. Owens</i>	Date Considered	11/10/04
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				Examiner Name	D. Owens
Sheet	4	of	7	Attorney Docket Number	740756-2646

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS		
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume/issue number(s), publisher, city and/or country where published.
21/2		T. TAKESHITA et al., "Study of ECR Hydrogen Plasma Treatment on Poly-Si Thin Film Transistors" Japanese Journal of Applied Physics, Vol. 27, No. 11, November 1988, pp. L2118-L2120, Tokyo, JP.
		S. Wolf & R.N. Tauber, "Silicon Processing of the VLSI ERA", Lattice Press, 1286, pp. 168-199, 334-335, Vol. I.
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		S. Ghandhi, VLSI FABRICATION PRINCIPLES., 1983, Wiley & Sons, P. 388-391.
		M. Morita et al., Appl. Phys. Lett., 49(86) 699 "F ENHANCED OXIDATION OF Si UNDER EXCIMER LASER...".
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		S. Suyama et al., IEEE Trans. Electron Dev., 34(10) (1987) 2124, "...MOSFET's Utilizing Oxygen-Argon Sputter-Deposited Gate Oxide Films", October, 1987.
		T.L. Kamins et al., IEEE Electron Dev. Lett. Vol EDL-1, No. 8, 159 "Hydrogenation of transistors fabricated in Polycrystalline-Silicon Films", August, 1980.
		Katoda, "Estimation of a Semiconductor by a Laser Raman Spectroscopy", Published by Tokyo University, 1988, pp. 67-75 (in Japanese with Concise English Statement).
21/2		Baker et al., "The Influence of Fluorine on Threshold Voltage Instabilities In P+ Polysilicon gated P-Channel MOSFETs", IEEE, 1989, IEDM, pages 443-446.

Examiner Signature	<i>D. Owens</i>	Date Considered	11/10/04
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		Country Code ¹	Number ² (If known)			

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS		
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
DW9		Wright and Saraswat, "The Effect of Fluorine in Silicon Dioxide Gate Dielectrics", IEE Transactions on Electron Devices, Vol. 36, No. 5, May 1989, pages 879-889.
		MacWilliams, Halle and Zietlow, "Improved Hot-Carrier Resistance With Fluorinated Gate Oxides", IEEE Electron Device Letters, Vol. 11, No. 1, January 1990, pages 3-5.
		Nishio et al., "Radiation Hardened Micron and Submicron MOSFETS Containing Fluorinated Oxides, IEEE Transactions on Nuclear Science, Vol. 36, no. 6, December 1989, pages 2116-2123.
DW9		Wright, Kasai, Inoue, Saraswat, "Hot-Electron Immunity of SiO ₂ Dielectrics with Fluorine Incorporation", IEEE Electron Device Letters, Vol. 10, No. 8, August 1989.

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Form PTO-1449 (Rev. 8-83)		U.S. Department of Commerce Patent and Trademark		Attorney Docket: 740736-2646		Sheet 6 of 7 Serial No. 10/642,305		
INFORMATION DISCLOSURE STATEMENT								
(Use several sheets if necessary)								
				Applicant: Hongyong ZHANG et al.				
				Filing Date: August 18, 2003		Group: 2811		
U.S. PATENT DOCUMENTS								
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)		
DWO	4,377,421	03/22/83	Wada et al					
	4,561,906	12/31/85	Calder et al					
	4,619,034	10/28/86	Janning					
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	4,698,486	10/06/87	Sheets					
	4,814,292	03/21/89	Sasaki et al					
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	4,882,295	11/21/89	Czubatyj et al					
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	5,329,140	07/12/94	Sera					
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DWO	G. Kawachi et al., "Large-Area Doping Process for Fabrication of poly-Si Thin Film Transistors Using Bucket Ion Source and XeCl Excimer Laser Annealing", Japanese Journal of Applied Physics, Vol. 29, No. 12, December 1990, pp. L2370-L2372							
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Form PTO-1449
(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark OfficeAttorney Docket: 740756-
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Serial No. 10/642,305

INFORMATION DISCLOSURE STATEMENT

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Applicant: Hongyong ZHANG et al.

Filing Date: August 18, 2003

Group: 2811

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
<i>20/09</i>	57-109377	07/07/82	Japan			Abstract	
	58-002073	01/07/83	Japan			Full	
	58-182816	10/25/83	Japan			Abstract	
	59-040580	03/06/84	Japan			Abstract	
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Examiner

Ralph W. Owe

Date Considered

11/10/04

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